

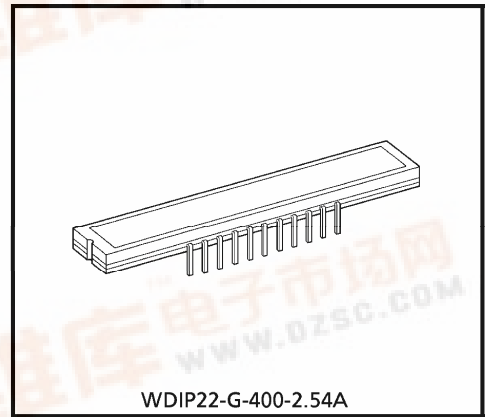
TOSHIBA

TCD1208AP

TOSHIBA CCD LINEAR IMAGE SENSOR CCD(Charge Coupled Device)

TCD1208AP

The TCD1208AP is a high sensitive and low dark current 2160- element image sensor. The sensor can be used for facsimile, imagescanner and OCR. The device contains a row of 2160 photodiodes, which provide a 8 lines/mm (200 DPI) across a B4 size paper. The device is operated by 5V (pulse), and 5V power supply.



Weight : 2.7g (Typ.)

FEATURES

- Number of Image Sensing Elements : 2160
- Image Sensing Element Size : 14μm by 14μm on 14μm centers
- Photo Sensing Region : High sensitive, Low dark current
- Clock : 2 phase (5V)
- Package : 22 pin DIP (T-CAPP)

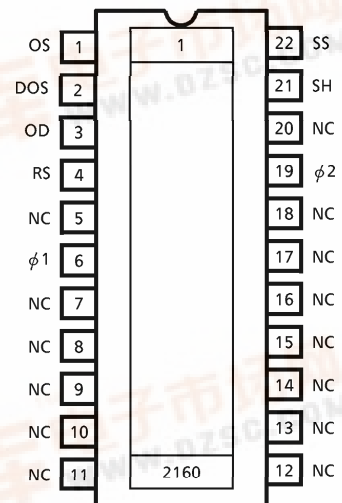
TOSHIBA-CCD-ADVANCED-PLASTIC-PACKAGE

MAXIMUM RATINGS (Note 1)

| CHARACTERISTIC | SYMBOL | RATING | UNIT |
|-----------------------|------------|----------|------|
| Clock Pulse Voltage | V_{ϕ} | - 0.3~8 | V |
| Shift Pulse Voltage | V_{SH} | | |
| Reset Pulse Voltage | V_{RS} | | |
| Power Supply Voltage | V_{OD} | | |
| Operating Temperature | T_{opr} | - 25~60 | °C |
| Storage Temperature | T_{stg} | - 40~100 | °C |

(Note 1) All voltage are with respect to SS terminals (Ground).

PIN CONNECTIONS



(TOP VIEW)

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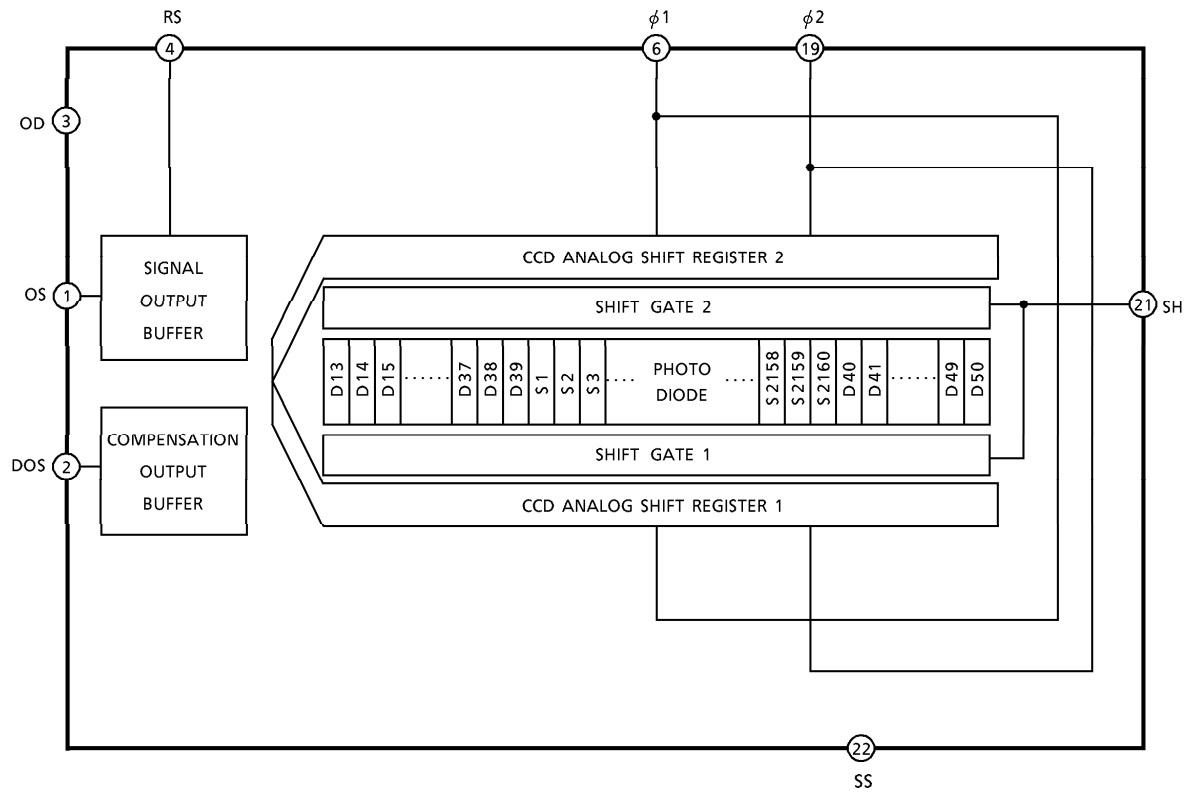
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CIRCUIT DIAGRAM



PIN NAMES

| | |
|----------|---------------------|
| $\phi 1$ | Clock (Phase 1) |
| $\phi 2$ | Clock (Phase 2) |
| SH | Shift Gate |
| RS | Reset Gate |
| OS | Signal Output |
| DOS | Compensation Output |
| OD | Power |
| SS | Ground |
| NC | Non Connection |



OPTICAL / ELECTRICAL CHARACTERISTICS

(Ta = 25°C, VOD = 5V, Vφ = VSH = VRS = 5V (PULSE), fφ = 0.5MHz, fRS = 1MHz, LOAD RESISTANCE = 100kΩ, tINT (INTEGRATION TIME) = 10ms, LIGHT SOURCE = DAYLIGHT FLUORESCENT LAMP)

| CHARACTERISTIC | SYMBOL | MIN. | TYP. | MAX. | UNIT | NOTE |
|--------------------------------|----------|------|------|------|----------|-----------|
| Sensitivity | R | 82 | 110 | 138 | V / lx·s | (Note 2) |
| Photo Response Non Uniformity | PRNU (1) | — | — | 10 | % | (Note 3) |
| | PRNU (3) | — | 7 | 16 | mV | (Note 10) |
| Register Imbalance | RI | — | — | 3 | % | (Note 4) |
| Saturation Output Voltage | VSAT | 0.6 | 1.5 | — | V | (Note 5) |
| Saturation Exposure | SE | — | 0.01 | — | lx·s | (Note 6) |
| Dark Signal Voltage | VDRK | — | 2 | 6 | mV | (Note 7) |
| Dark Signal Non Uniformity | DSNU | — | 3 | 7 | mV | (Note 7) |
| DC Power Dissipation | PD | — | 50 | 100 | mW | |
| Total Transfer Efficiency | TTE | 92 | — | — | % | |
| Output Impedance | ZO | — | — | 1 | kΩ | |
| Dynamic Range | DR | — | 750 | — | — | (Note 8) |
| DC Signal Output Voltage | VOS | 3 | 3.5 | 4.5 | V | (Note 9) |
| DC Compensation Output Voltage | VDOS | 3 | 3.5 | 4.5 | V | (Note 9) |
| DC Mismatch Voltage | VOS-VDOS | — | 50 | 100 | mV | (Note 11) |
| Random Noise | NDσ | — | 1.7 | — | mV | (Note 12) |

(Note 2) Sensitivity for 2854K W-Lamp is 330V / lx·s (Typ.)

Sensitivity for LED (567nm) is 71V / lx·s (Typ.)

(Note 3) Measured at 50% of SE (Typ.)

$$\text{Definition of PRNU: } PRNU = \frac{\Delta x}{\bar{x}} \times 100 (\%)$$

Where \bar{x} is average of total signal outputs and Δx is the maximum deviation from \bar{x} under uniform illumination.

(Note 4) Measured at 50% of SE (Typ.)

RI is defined as follows:

$$RI = \frac{\sum_{n=1}^{2159} |x_n - x_{n+1}|}{2159 \times \bar{x}} \times 100 (\%)$$

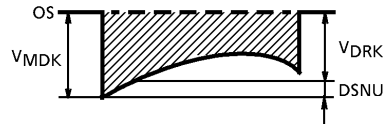
Where x_n and x_{n+1} are signal outputs of each pixel. \bar{x} is average of total signal outputs.

(Note 5) VSAT is defined as minimum Saturation Output Voltage of all effective pixels.

(Note 6) Definition of SE : $SE = \frac{VSAT}{R}$



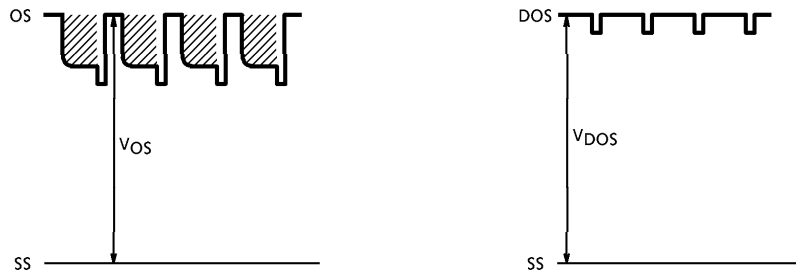
(Note 7) V_{DRK} is defined as average dark signal voltage of all effective pixels. DSNU is defined as different voltage between V_{DRK} and V_{MDK} , when V_{MDK} is maximum dark voltage.



(Note 8) Definition of DR : $DR = \frac{V_{SAT}}{V_{DRK}}$

V_{DRK} is proportional to t_{INT} (Integration time). So the shorter t_{INT} is, the wider DR is.

(Note 9) DC Signal Output Voltage and DC Compensation Output Voltage are defined as follows:



(Note 10) PRNU (3) is defined as maximum voltage with next pixel where measured 5% of SE (Typ.).

(Note 11) $V_{OD} = 4.7V$ DC Mismatch Voltage.



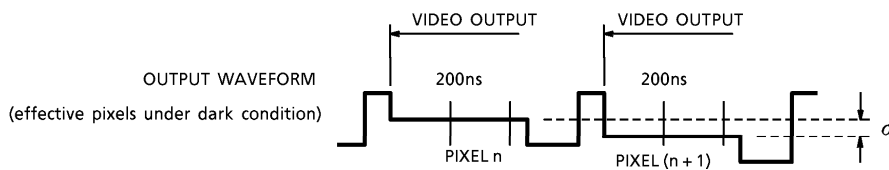
(Note 12)

1. DEFINITION

Random noise is defined as the standard deviation (sigma) of the output level difference between two adjacent effective pixels under no illumination (i.e. dark condition) calculated by the following procedure.

2. CALCULATION PROCEDURE

The following is the calculation procedure of random noise.



- 1) Two adjacent pixels (pixel n and n + 1) in one reading are fixed as measurement points.
- 2) Each of the output levels at video output period is averaged over 200 nanosecond period to get V_n and V_{n+1} .
- 3) V_{n+1} is subtracted from V_n to get ΔV .
$$\Delta V = V_n - V_{n+1}$$
- 4) The standard deviation of ΔV is calculated after procedure 2) and 3) are repeated 30 times (30 readings).

$$\overline{\Delta V} = \frac{1}{30} \sum_{i=1}^{30} |\Delta V_i| \quad \sigma = \sqrt{\frac{1}{30} \sum_{j=1}^{30} (|\Delta V_j| - \overline{\Delta V})^2}$$

- 5) Procedure 2), 3) and 4) are repeated 10 times to get 10 sigma values.

$$\overline{\sigma} = \frac{1}{10} \sum_{j=1}^{10} \sigma_j$$

- 6) $\overline{\sigma}$ value calculated using the above procedure is observed $\sqrt{2}$ times larger than that measured relative to the ground level. So we specify the random noise as the following.

$$\text{Random noise } (N_{D\sigma}) = \frac{1}{\sqrt{2}} \overline{\sigma}$$



OPERATING CONDITION

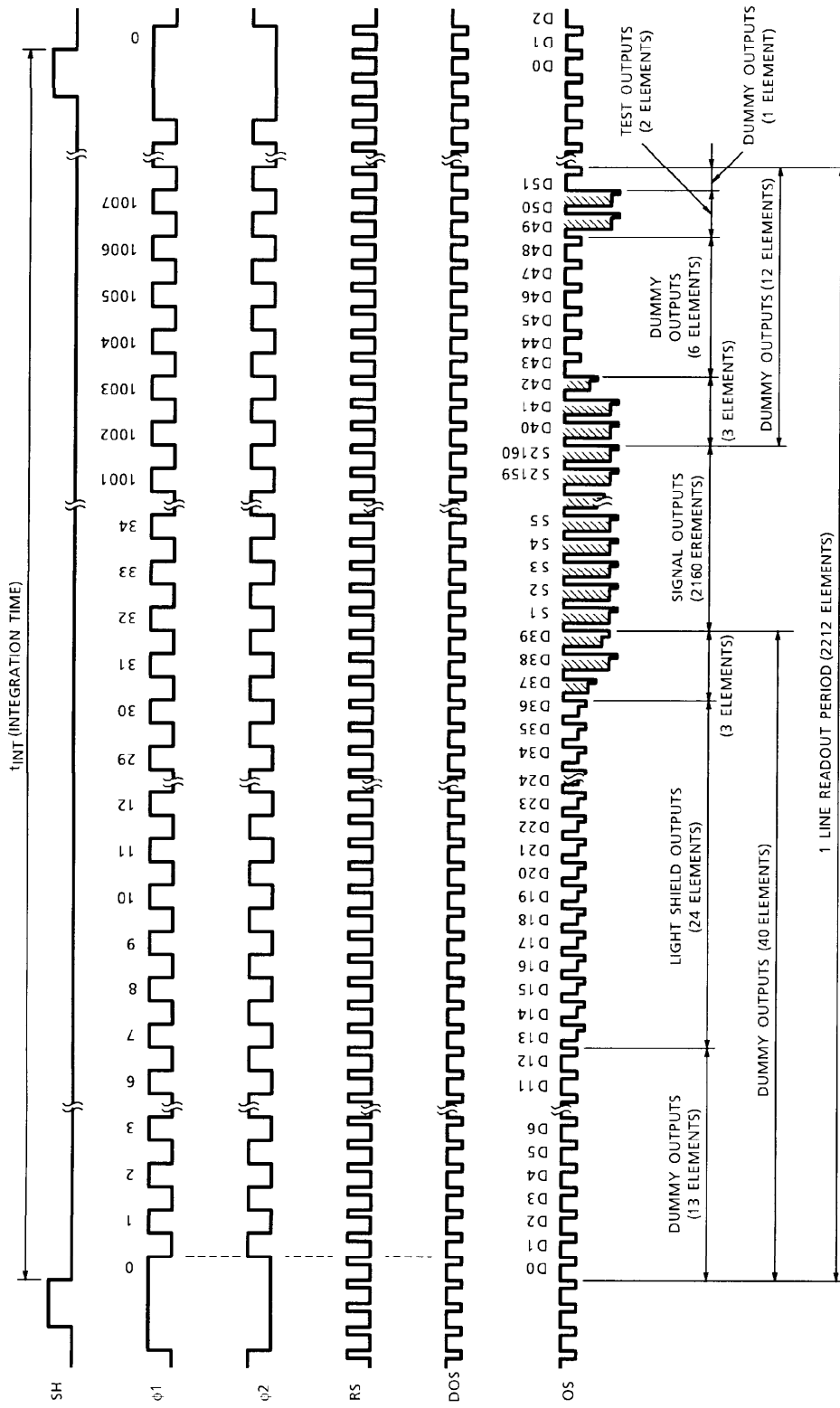
| CHARACTERISTIC | | SYMBOL | MIN. | TYP. | MAX. | UNIT |
|----------------------|-----------|------------|------|------|------|------|
| Clock Pulse Voltage | "H" Level | V_{ϕ} | 4.5 | 5 | 5.5 | V |
| | "L" Level | | 0 | 0 | 0.3 | |
| Shift Pulse Voltage | "H" Level | V_{SH} | 4.5 | 5 | 5.5 | V |
| | "L" Level | | 0 | 0 | 0.3 | |
| Reset Pulse Voltage | "H" Level | V_{RS} | 4.7 | 5 | 5.5 | V |
| | "L" Level | | 0 | 0 | 0.3 | |
| Power Supply Voltage | | V_{OD} | 4.7 | 5.0 | 5.3 | V |

CLOCK CHARACTERISTICS (Ta = 25°C)

| CHARACTERISTIC | SYMBOL | MIN. | TYP. | MAX. | UNIT |
|------------------------|------------|------|------|------|------|
| Clock Pulse Frequency | f_{ϕ} | 0.15 | 0.5 | 1.0 | MHz |
| Reset Pulse Frequency | f_{RS} | 0.3 | 1.0 | 2.0 | MHz |
| Clock Capacitance | C_{ϕ} | — | 200 | 300 | pF |
| Shift Gate Capacitance | C_{SH} | — | 100 | 200 | pF |
| Reset Gate Capacitance | C_{RS} | — | 10 | 30 | pF |

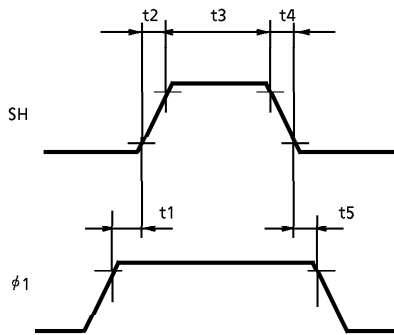


TIMING CHART

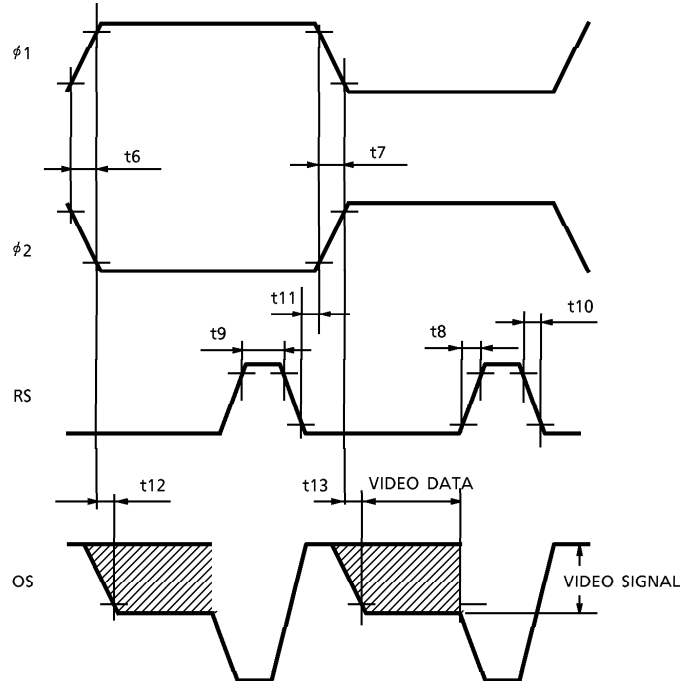


TIMING REQUIREMENTS

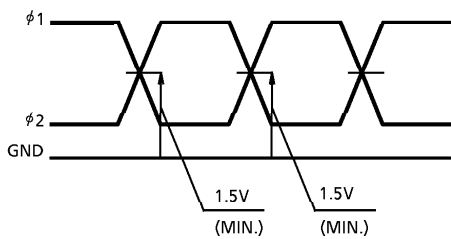
SH, $\phi 1$ Timing



$\phi 1, \phi 2, RS, OS$ Timing



$\phi 1, \phi 2$ Cross Point



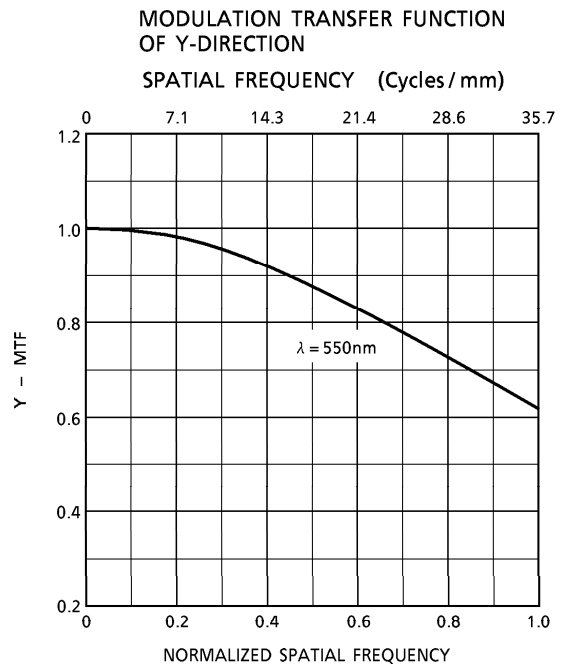
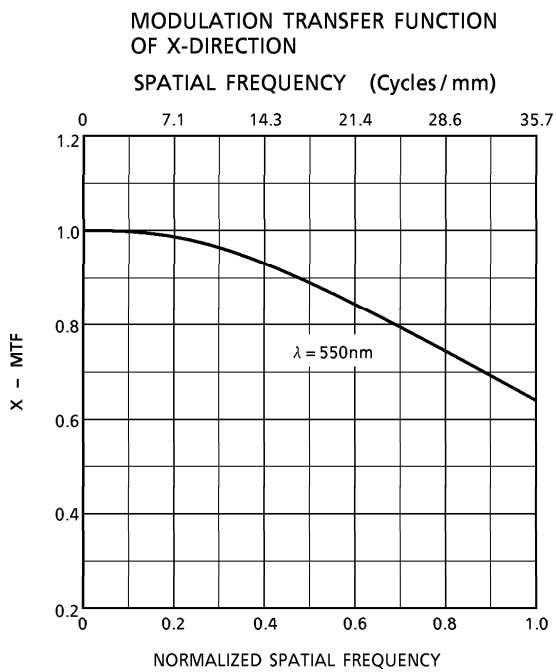
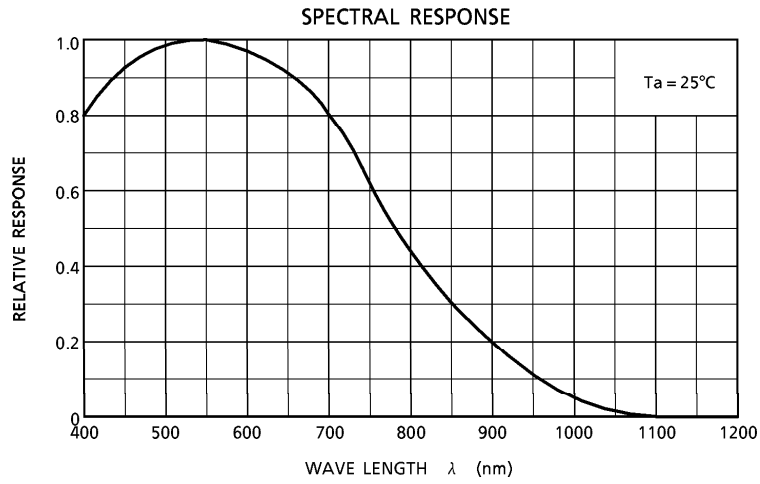
| CHARACTERISTIC | SYMBOL | MIN. | TYP. (Note 13) | MAX. | UNIT |
|--|----------|------|-------------------|------|------|
| Pulse Timing of SH and $\phi 1$ | t1, t5 | 0 | 100 | — | ns |
| SH Pulse Rise Time, Fall Time | t2, t4 | 0 | 50 | — | ns |
| SH Pulse Width | t3 | 500 | 1000 | — | ns |
| $\phi 1 \phi 2$ Pulse Rise Time, Fall Time | t6, t7 | 0 | 60 | 100 | ns |
| RS Pulse Rise Time, Fall Time | t8, t10 | 0 | 20 | — | ns |
| RS Pulse Width | t9 | 40 | 250 | — | ns |
| Pulse Timing of $\phi 1, \phi 2$ and RS | t11 | 230 | — | — | ns |
| Video Data Delay Time (Note 14) | t12, t13 | — | 150 | — | ns |

(Note 13) TYP. is the case of $f_{RS} = 1\text{MHz}$

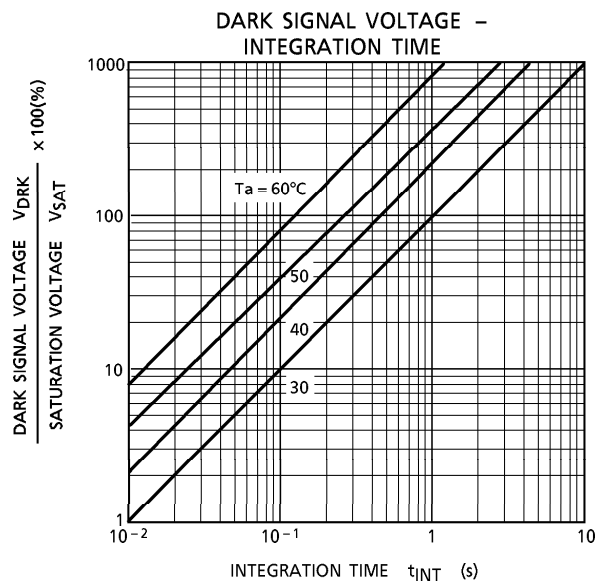
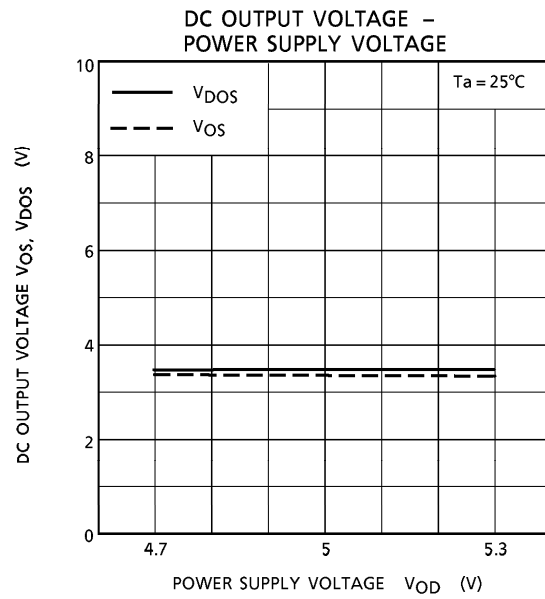
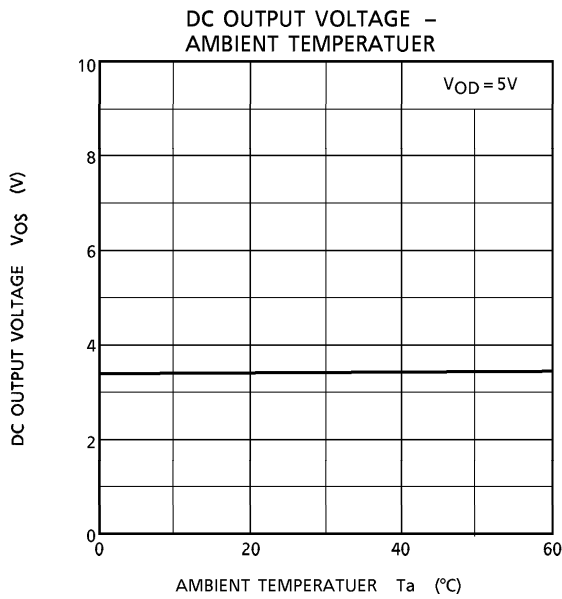
(Note 14) Load Resistance is $100\text{k}\Omega$



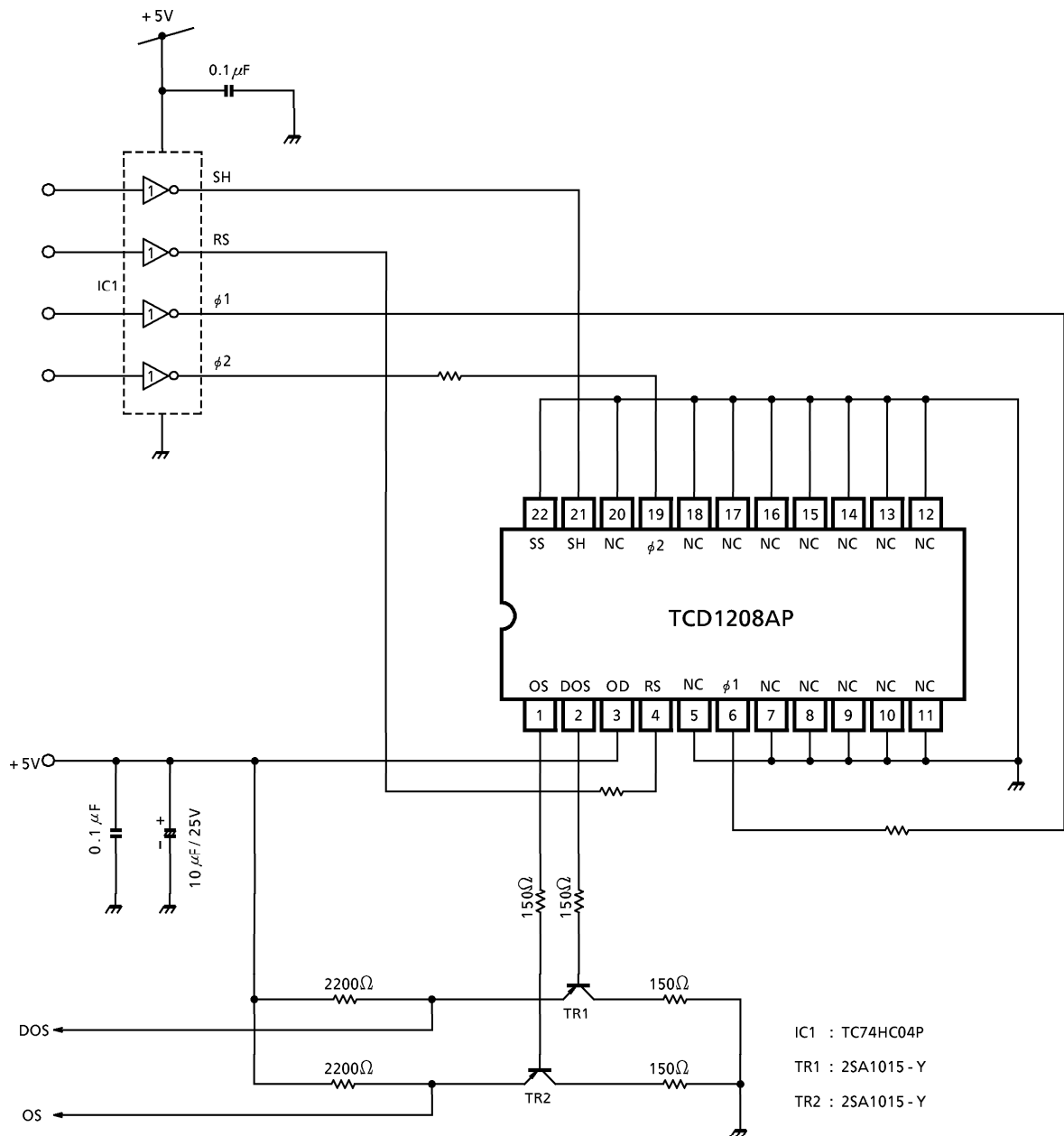
TYPICAL PERFORMANCE CURVES



TYPICAL PERFORMANCE CURVES



TYPICAL DRIVE CIRCUIT



CAUTION**1. Window Glass**

The dust and stain on the glass window of the package degrade optical performance of CCD sensor.

Keep the glass window clean by saturating a cotton swab in alcohol and lightly wiping the surface, and allow the glass to dry, by blowing with filtered dry N₂.

Care should be taken to avoid mechanical or thermal shock because the glass window is easily to damage.

2. Electrostatic Breakdown

Store in shorting clip or in conductive foam to avoid electrostatic breakdown.

3. Incident Light

CCD sensor is sensitive to infrared light.

Note that infrared light component degrades resolution and PRNU of CCD sensor.

4. Lead Frame Forming

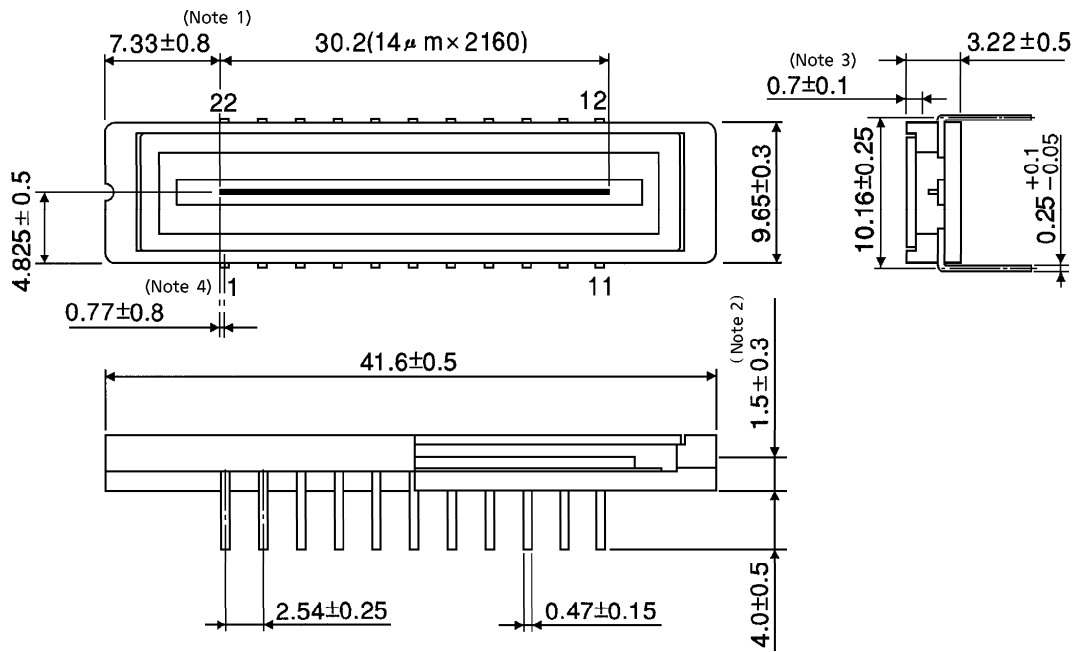
Since this package is not stout against mechanical stress, you should not reform the lead frame.

We recommend to use a IC-inserter when you assemble to PCB.



OUTLINE DRAWING
WDIP22-G-400-2.54A

Unit : mm



- (Note 1) No. 1 SENSOR ELEMENT (S1) TO EDGE OF PACKAGE.
- (Note 2) TOP OF CHIP TO BOTTOM OF PACKAGE.
- (Note 3) GLASS THICKNES (n = 1.5)
- (Note 4) No. 1 SENSOR ELEMENT (S1) TO CENTER OF No. 1 PIN.

Weight : 2.7g (Typ.)

